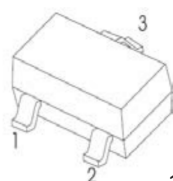


FEATURES

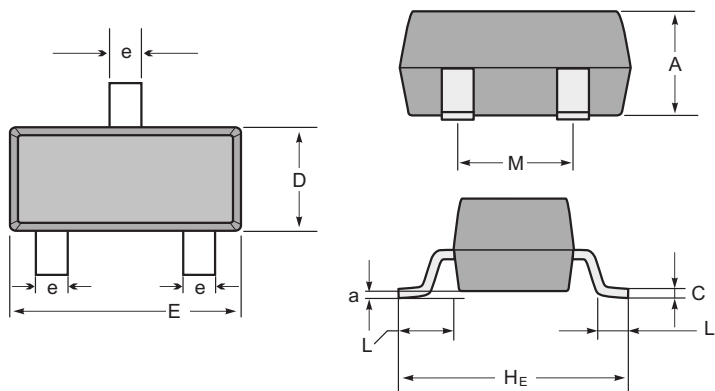
- Collector Current: $I_C=0.5A$



1.BASE
2.EMITTER
3.COLLECTOR

Marking

Type number	Marking code
S8550	2TY



SOT-23 mechanical data

UNIT		A	C	D	E	H _E	e	M	L	L ₁	a
mm	max	1.1	0.15	1.4	3.0	2.6	0.5	1.95	0.55 (ref)	0.36 (ref)	0.0
	min	0.9	0.08	1.2	2.8	2.2	0.3	1.7			0.15
mil	max	43	6	55	118	102	20	77	22 (ref)	14 (ref)	0.0
	min	35	3	47	110	87	12	67			6

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector–Base Voltage	V_{CBO}	-40	V
Collector–Emitter Voltage	V_{CEO}	-25	V
Emitter–Base Voltage	V_{EBO}	-5	V
Collector Current — Continuous	I_C	-0.5	A
Collector Dissipation	P_C	0.3	W
Operation Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	°C

CLASSIFICATION OF h_{FE1}

Rank	L	H	J
Range	120-200	200-350	300-400

MMBT8550D

CLASSIFICATION OF h_{FE1}

Rank	L	H	J
Range	120-200	200-350	300-400

ELECTRICAL CHARACTERISTICS (TA = 25°C unless otherwise noted.)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{ mA}, I_B = 0$	-25		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB} = -40\text{V}, I_E = 0$		-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -20\text{V}, I_B = 0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -3\text{V}, I_C = 0$		-0.1	μA
DC current gain	h_{FE1}	$V_{CE} = -1\text{V}, I_C = -50\text{mA}$	120	400	
	h_{FE2}	$V_{CE} = -1\text{V}, I_C = -500\text{mA}$	50		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500\text{mA}, I_B = -50\text{mA}$		-0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500\text{mA}, I_B = -50\text{mA}$		-1.2	V
Transition frequency	f_T	$V_{CE} = -6\text{V}, I_C = -20\text{mA}, f = 30\text{MHz}$	150		MHz

RATING AND CHARACTERISTIC CURVES (MMBT8550D)

